



**Silicon solar cells efficiencies are limited by bad contacts. Can we use inverse design to find a better "hole-selective contact"?**

### Back to basics

#### How do solar photovoltaics (PV) work?

**Solar cell**  
 light → absorber converts light to electricity → current J

**Why contacts?**  
 PV efficiency is only as good as its weakest link! An absorber must be contacted on both sides for charge to transfer

Ugh... the absorber gets all the hype. But without us contacts, it would be useless!

**Solar module**  
 Solar cell → encapsulation → metal → current J

**PV efficiency**  
 $\eta = \frac{\text{Energy out}}{\text{Energy in}}$

**Silicon heterojunction (SHJ)**  
 Theory  $\eta = 32.7\%$   
 Cell  $\eta = 26.7\%$   
 Module  $\eta \sim 20\%$   
 10 years  $\eta \sim 17\%$

10% of market share by 2024  
 But discrepancy with theoretical efficiency! Why?

### Simulating materials properties

**Multi-parameter analysis is key**

VB and doping must be optimized together

**Band bending**  
 Performance drops can be explained by recombination and loss of quasi-fermi level splitting

**Simulated performance**  
 Heatmap of Efficiency (%) vs. Hole doping  $N_A$  ( $\text{cm}^{-3}$ ) and Voltage (V)

**Current-voltage (J-V) curve**  
 Graph of current density J ( $\text{mA cm}^{-2}$ ) vs. Voltage (V) for different hole doping levels.

**Defects and thickness matter**  
 Interfacial defects ( $D_i$ ) and Thickness ( $t$ ) affect performance.

**Mobility less important**  
 Hole mobility ( $\mu_h$ ) is less critical than other parameters.

**These design parameters and their tolerances can now be used as inputs for inverse design searches**

### Conclusions

**Developed an inverse design approach**

**COMPUTATION**  
 Develop metrics, Evaluate metrics, Scope inputs, Assess physics, Simulate tolerances, Measure devices, Synthesize candidates, Screen using metrics, Identify new candidates

**EXPERIMENT**  
 Fabricate devices

**Hole selective contact discovery**

**Next steps**  
 Perform full screen  
 Synthesize ZnTe, BeTe, other outputs  
 Optimize devices  
 Apply approach to other PV (CdTe, GaAs)

We've been missing a multi-parameter approach!

Computation and experiment must inform each other!

### References

[1] NREL, (2020). "Best Research-Cell Efficiency Chart."  
 [2] Woods-Robinson, R., et al. (2020). *Journal of photovoltaics*  
 [3] Woods-Robinson, R., et al. (2021). *2020 47th IEEE Photovoltaic Specialists Conference (PVSC)*  
 [4] Woods-Robinson, R., et al. (2020). *Chemical Reviews*, 120(9), 4007-4055.

### Nanoscale barriers

#### Challenges in SHJ

Parasitic absorption: The top contact is not transparent enough! Band gap  $E_G$  is too small

Can we find a transparent hole selective contact, aka "p-layer", to replace (p) a-Si?

**Design requirements**

- p-type material (how much?)
- More transparent than a-Si
- VB "aligned" with c-Si's VB; no contact resistance
- Low interface recombination

But these are qualitative...

### Experimental validation

**Test-case**  
 Combinatorial sputter growth of  $\text{NiO}_x$  on (p) a-Si. Parameters:  $x = 0, 1, 5, 9$ .

**PV efficiency**  
 Low, but predictably low! Comparison of experimental and simulated J-V curves for different  $\text{NiO}_x$  compositions.

**Valence band offsets**  
 Energy level diagrams showing the alignment of valence bands at the interface between different materials.

**Interfacial reactions**  
 Reaction at interface between  $\text{NiO}_x$  and the substrate.

**Hypothesis:**  
 $\text{SiO}_2$  at interface,  $D_i \uparrow$ ,  $\text{FF} \downarrow$ ,  $V_{oc} \downarrow$

**Experimental trends corroborate VB position and materials properties in our simulations**

### Design new materials

#### Updated design requirements

- Band gap  $E_G > 3$  eV (as expected)
- $E_{VB}$  aligned to 5.5 eV: w/in  $\pm 0.3$  eV for  $N_A > 10^{18} \text{ cm}^{-3}$ , or w/in  $\pm 0.1$  eV for  $N_A > 10^{16} \text{ cm}^{-3}$  for  $D_i < 10^{11}$
- Higher  $D_i$ : sharper  $E_{VB}$  and  $N_A$  requirements
- Mobility  $> 0.05 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$  (less restrictive)

**Inverse design "funnel"**  
 Input: All crystalline semiconductors  
 1. Has been synthesized  
 2. Band gap  $E_G > 3$  eV  
 3. p-type dopable  
 4. VB w/in  $\pm 0.3$  eV of a-Si  
 5. Stable interface  
 Output: candidates for SHJ hole selective top contacts

**Valence band offsets**  
 Energy level diagrams for various materials.

**Interfacial reactions**  
 Reaction at interface between  $\text{NiO}_x$  and various materials.

**We can use our findings to inform materials discovery of a p-type hole selective top-contact for SHJ**

### Scientist-society barriers

**How can we connect with our communities to build trust and communicate these challenges?**

**Cycle for Science**, founded by Rachel Woods-Robinson (Berkeley) and Elizabeth Case (Columbia), takes scientists on bicycle trips around the world to stop in classrooms and teach hands-on lessons about renewable energy and climate change.

**DIY solar cells (Netherlands 2019)**  
 I'm a solar cell made by students out of blackberries and graphite (pencil) contacts!

**DIY glaciers (NY 2019)**  
 I'm "glacier goo"

**"Sol cycle" (cross-USA 2015, CA 2017)**  
 I'm a mini, 3D printed, solar bicycle!

**Are you a scientist interested in joining a future trip? We'd love to have you! Reach out at [wecycleforscience@gmail.com](mailto:wecycleforscience@gmail.com)**

### Theory-experiment barriers

**Status quo**  
 I'm a new shiny material! Alas... I don't like SHJ. Predictions haven't worked... are we designing wrong?

**"Inverse design"**  
 1. Vary material parameters  
 2. Simulate optimal design parameters  
 3. Validate with experiment  
 4. Discover based on these parameters  
 New materials from inverse design!